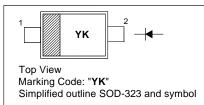
## **SCHOTTKY BARRIER DIODE**

## **Features**

- Low power rectified
- Silicon epitaxial type
- High reliability

#### **PINNING**

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	30	V
Forward Current	I <sub>F</sub>	0.2	А
Repetitive Peak Forward Current	I <sub>FRM</sub>	0.5	А
Non-Repetitive Peak Forward Current (8.3 ms)	I <sub>FSM</sub>	1	А
Power Dissipation	$P_D$	150	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	Ts	- 55 to + 150	°C

# Characteristics at $T_a = 25$ °C

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10$ mA at $I_F = 30$ mA	V <sub>F</sub>	0.4 0.5	V
Reverse Current at V <sub>R</sub> = 30 V	I <sub>R</sub>	1	μΑ
Total Capacitance at $V_R = 1 \text{ V}$ , $f = 1 \text{ MHz}$	Ст	10	pF







listed on the Hong Kong Stock Exchange, Stock Code: 724)

Fig. 1  $I_F$ - $V_F$ 

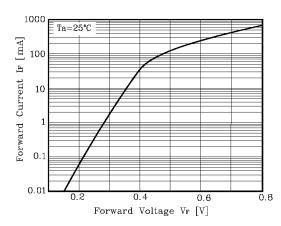


Fig. 2  $I_R$  - $V_R$ 

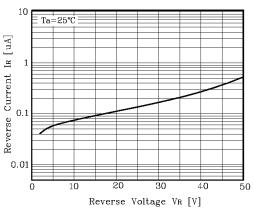
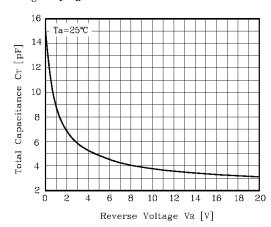
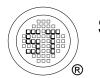


Fig. 3  $C_T$ - $V_R$ 











## **PACKAGE OUTLINE**

Plastic surface mounted package; 2 leads

**SOD-323** 

